



US00D729250S

(12) **United States Design Patent**
Han

(10) **Patent No.:** **US D729,250 S**

(45) **Date of Patent:** **** May 12, 2015**

(54) **SEMICONDUCTOR MEMORY DEVICE**

(56) **References Cited**

(71) Applicant: **Samsung Electronics Co., Ltd.**,
Suwon-si (KR)

U.S. PATENT DOCUMENTS

(72) Inventor: **Jae-hwan Han**, Seoul (KR)

(73) Assignee: **Samsung Electronics Co., Ltd.**,
Suwon-si (KR)

(**) Term: **14 Years**

(21) Appl. No.: **29/492,369**

(22) Filed: **May 30, 2014**

Related U.S. Application Data

(63) Continuation-in-part of application No. 13/954,341,
filed on Jul. 30, 2013.

(51) **LOC (10) Cl.** **14-02**

(52) **U.S. Cl.**
USPC **D14/436**

(58) **Field of Classification Search**
USPC D14/435-438, 478-483, 474, 475, 335,
D14/496, 125, 188, 192, 204, 217, 265, 433,
D14/432, 242; 235/441, 443, 487, 492, 493,
235/495, 486, 451, 479, 453; 361/737, 679,
361/752, 736, 728, 796, 797, 729, 730,
361/725-727, 740, 747, 759, 801, 816, 738,
361/766, 799, 807, 829; 257/678, 679, 693,
257/E23.064; 439/946, 948, 159, 628, 638,
439/630, 267, 260, 945, 95, 140, 101, 67,
439/76.1, 108, 147, 148; 174/250, 260,
174/52.1, 52.2, 35 R, 51; 710/300-303, 62,
710/74; 438/121; D21/332, 333;
455/344-351; 369/1, 4, 6-12; 381/119,
381/120; 700/94; 345/156, 184; 312/233.2;
206/706, 701; 360/129, 132, 133, 135;
D13/182

See application file for complete search history.

D213,783	S	*	4/1969	Laybourn et al.	D14/435
3,659,821	A	*	5/1972	Sakamoto et al.	249/84
4,214,292	A	*	7/1980	Johnson	361/721
4,332,537	A	*	6/1982	Slepcevic	425/121
4,647,123	A	*	3/1987	Chin et al.	439/61
D303,922	S	*	10/1989	Russell et al.	D8/321
D304,448	S	*	11/1989	De La Cruz et al.	D14/436
4,941,841	A	*	7/1990	Darden et al.	361/679.39
D313,229	S	*	12/1990	Audebert et al.	D14/436
4,979,075	A	*	12/1990	Murphy	361/679.32
D313,410	S	*	1/1991	Audebert et al.	D14/436
5,061,845	A	*	10/1991	Pinnavaia	235/492
5,715,146	A	*	2/1998	Hoppal	361/796
5,757,618	A	*	5/1998	Lee	361/679.32
5,766,535	A	*	6/1998	Ong	264/272.15
5,826,719	A	*	10/1998	Chen	206/373
5,865,310	A	*	2/1999	Lee	206/308.1
5,932,254	A	*	8/1999	Mitchell et al.	425/117
D416,885	S	*	11/1999	Hirai et al.	D14/436
6,011,741	A	*	1/2000	Wallace et al.	365/221
6,052,278	A	*	4/2000	Tanzer et al.	361/679.33
RE36,695	E	*	5/2000	Holt	312/265.6
D431,568	S	*	10/2000	Chan et al.	D14/436
6,129,556	A	*	10/2000	Sihn et al.	439/61

(Continued)

Primary Examiner — Susan Moon Lee

(74) *Attorney, Agent, or Firm* — Sughrue Mion, PLLC

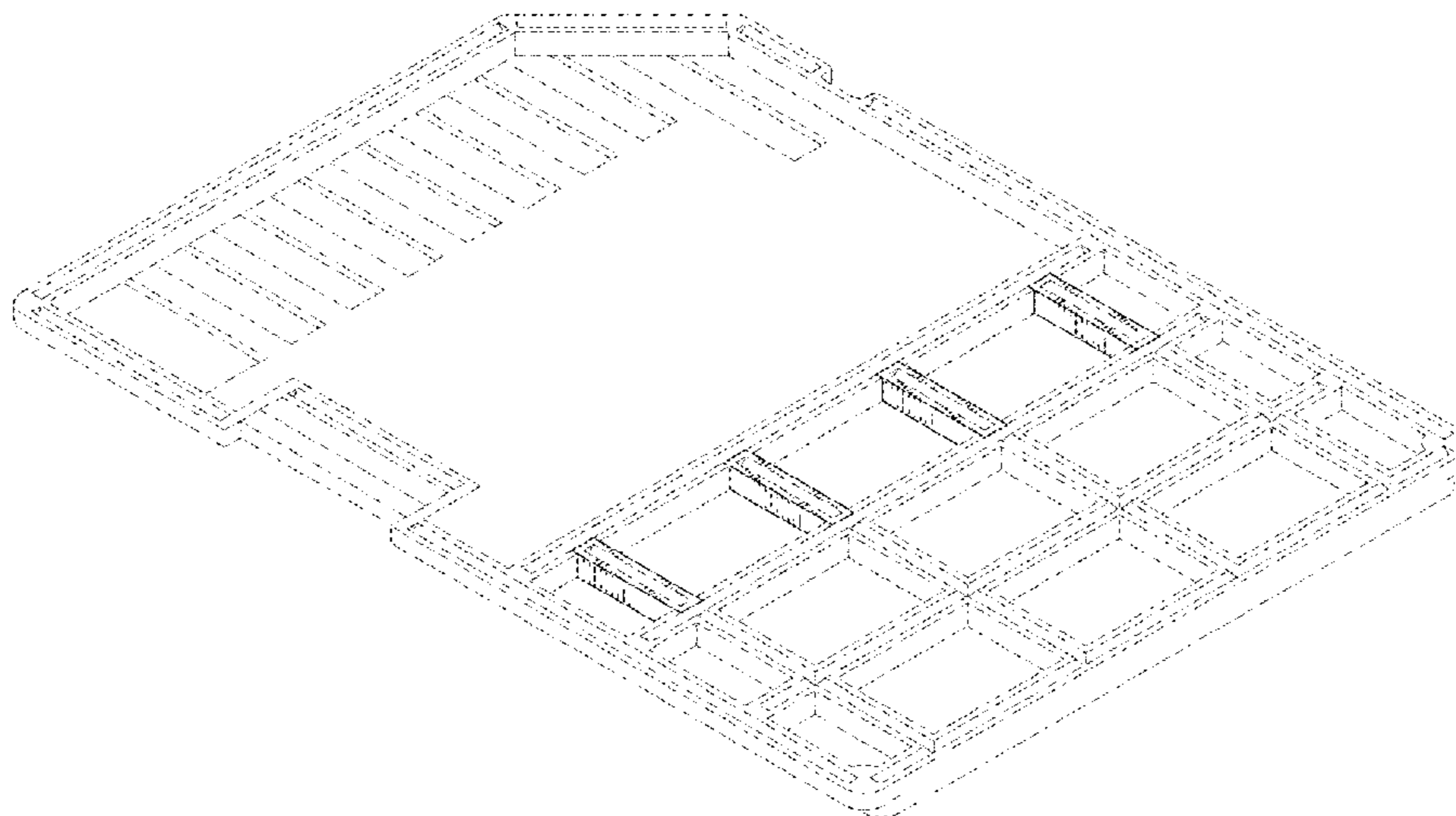
(57) **CLAIM**

The ornamental design for a semiconductor memory device,
as shown and described.

DESCRIPTION

FIG. 1 is a perspective view of a semiconductor memory device showing our new design; and, FIG. 2 is a top plan view thereof. Broken lines and unshaded portions entirely contained within broken line are not claimed.

1 Claim, 2 Drawing Sheets



(56)

References Cited

U.S. PATENT DOCUMENTS

6,173,843	B1 *	1/2001	Christensen et al.	211/41.17				
D437,856	S *	2/2001	Ohanian	D14/436				
6,295,565	B1 *	9/2001	Lee	710/301				
D449,835	S *	10/2001	Ohtani	D14/436				
6,305,921	B1 *	10/2001	Grams et al.	425/116				
6,315,540	B1 *	11/2001	Tsuruta	425/123				
6,333,635	B1 *	12/2001	Lee et al.	324/754.07				
6,357,603	B1 *	3/2002	Dingman	211/41.17				
D461,816	S *	8/2002	Caughlan et al.	D14/445				
D494,975	S *	8/2004	McClelland et al.	D14/435				
6,769,921	B1 *	8/2004	Broder et al.	439/74				
6,796,438	B2 *	9/2004	Mendoza	211/26				
6,844,651	B1 *	1/2005	Swift et al.	310/214				
7,008,240	B1 *	3/2006	Wang et al.	439/76.1				
7,059,871	B1 *	6/2006	Hsiao	439/76.1				
7,169,345	B2 *	1/2007	Murugan	264/272.15				
7,179,129	B1 *	2/2007	Hwang	439/630				
7,191,899	B2 *	3/2007	Garcia et al.	206/308.1				
7,210,967	B1 *	5/2007	Lee	439/630				
7,252,528	B1 *	8/2007	Tsao	439/327				
7,265,453	B2 *	9/2007	James et al.	257/787				
7,288,004	B1 *	10/2007	Hou et al.	439/630				
D554,644	S *	11/2007	Ogasawara	D14/439				
7,296,716	B2 *	11/2007	Mayzel	224/673				
7,306,159	B1 *	12/2007	Rochelo	235/492				
7,345,848	B2 *	3/2008	Liu et al.	360/133				
7,367,817	B1 *	5/2008	Liu et al.	439/76.1				
D570,981	S *	6/2008	McClelland	D23/370				
7,388,759	B2 *	6/2008	Chen et al.	361/801				
7,393,246	B2 *	7/2008	Chi	439/630				
7,408,789	B2 *	8/2008	Tao et al.	361/801				
7,414,859	B2 *	8/2008	Tao et al.	361/801				
D577,026	S *	9/2008	Wang et al.	D14/439				
7,440,288	B1 *	10/2008	Chang	361/755				
7,535,088	B2 *	5/2009	Ni et al.	257/679				
D615,983	S *	5/2010	Aoki	D14/436				
7,929,288	B1 *	4/2011	Ma et al.	361/679.32				
8,072,331	B2 *	12/2011	Narendra et al.	340/572.1				
8,382,215	B2 *	2/2013	Chen	312/223.2				
8,541,889	B2 *	9/2013	Kim	257/777				
2001/0013674	A1 *	8/2001	Shimizu et al.	264/511				
2002/0129527	A1 *	9/2002	Vaudreuil	40/655				
2002/0142640	A1 *	10/2002	Abe	439/260				
2004/0039854	A1 *	2/2004	Estakhri et al.	710/11				
2004/0089717	A1 *	5/2004	Harari et al.	235/441				
2004/0214371	A1 *	10/2004	Mahmood	438/106				
2005/0185371	A1 *	8/2005	Kuroda et al.	361/684				
2005/0254210	A1 *	11/2005	Grady et al.	361/695				
2006/0218777	A1 *	10/2006	Swift et al.	29/605				
2007/0001003	A1 *	1/2007	Lee et al.	235/435				
2007/0004285	A1 *	1/2007	Lee	439/638				
2007/0089999	A1 *	4/2007	Decker et al.	206/39				
2008/0075802	A1 *	3/2008	Chan et al.	425/588				
2009/0108993	A1 *	4/2009	Forster	340/10.1				
2009/0124108	A1 *	5/2009	Elliott et al.	439/345				
2010/0061050	A1 *	3/2010	Kah	361/679.21				
2010/0176206	A1 *	7/2010	Han et al.	235/492				
2010/0209761	A1 *	8/2010	Koh et al.	429/162				
2011/0092087	A1 *	4/2011	Jung et al.	439/159				
2013/0162280	A1 *	6/2013	Chung et al.	324/756.03				
2014/0078685	A1 *	3/2014	Lee et al.	361/730				
2014/0113460	A1 *	4/2014	Park et al.	439/39				

* cited by examiner

FIG. 1

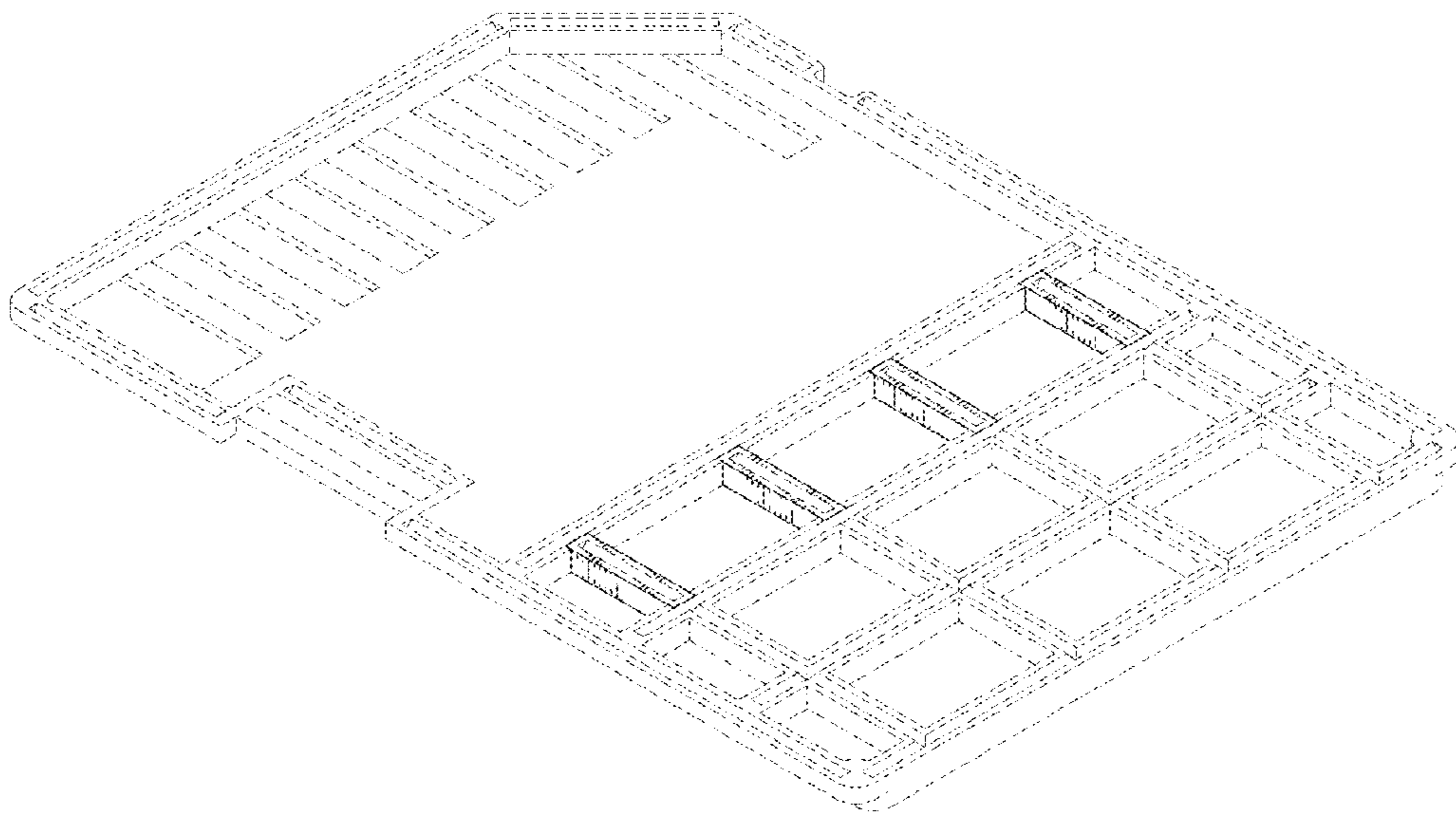


FIG. 2

